

Please amend the subject application as follows:

IN THE CLAIMS:

Please cancel claim 3 and accept amended claims 1, 4, 23, 25 and 26 and new claims 27-30 as follows:

1. (currently amended) A capacitor comprising:
a lower electrode formed on a semiconductor substrate;
a dielectric film stacked on the lower electrode; and
an upper electrode, comprising a first upper electrode and a second upper electrode, formed on the dielectric film, wherein:
the first upper electrode is formed by ~~chemical~~ physical vapor deposition without bias power applied to the semiconductor substrate and the second upper electrode is formed by physical ~~chemical~~ vapor deposition, ~~and~~
the capacitor is a concave-type capacitor.
2. (original) The capacitor of claim 1, wherein the upper electrode is made of one selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, ruthenium, platinum, iridium, and a combination thereof.
3. (canceled)
4. (currently amended) The capacitor of claim 1, wherein ~~the upper electrode includes a first upper electrode formed by the physical vapor deposition and a second upper electrode formed by the chemical vapor deposition and the first upper electrode~~

and the second upper electrode are sequentially stacked.

5. - 22. (canceled)

23. (currently amended) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film, wherein:

the upper electrode is formed by physical vapor deposition and one of chemical vapor deposition and atomic layer deposition, and

the upper electrode includes a first upper electrode formed by the physical vapor deposition without bias power applied to the semiconductor substrate and a second upper electrode formed by one of the chemical vapor deposition and the atomic layer deposition and

~~the capacitor is a concave type capacitor.~~

24. (canceled)

25. (currently amended) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film, wherein:

~~the upper electrode is formed by chemical vapor deposition and physical~~

~~vapor deposition, and includes a first upper electrode formed by physical vapor deposition without bias power applied to the semiconductor substrate and a second upper electrode; and~~
~~an anti-reflective layer formed on the second upper electrode.~~

26. (currently amended) The capacitor of claim 25, ~~wherein the capacitor is a concave-type capacitor~~ further comprising an anti-reflective layer formed on the second upper electrode.

27. (new) The capacitor of claim 25, wherein the upper electrode further includes a second upper electrode formed by chemical vapor deposition.

28. (new) The capacitor of claim 1, wherein the capacitor is a concave-type capacitor.

29. (new) The capacitor of claim 23, wherein the capacitor is a concave-type capacitor.

30. (new) The capacitor of claim 25, wherein the capacitor is a concave-type capacitor.